

Hyun Jae Kim

List of Publications by Year in descending order

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Version: 2024-02-01

415
papers

8,549
citations

47006

47
h-index

60623

81
g-index

420
all docs

420
docs citations

420
times ranked

5811
citing authors

#	ARTICLE	IF	CITATIONS
1	Rapid and selective green laser activation of InGaZnO thin-film transistors through metal absorption. Journal of Information Display, 2022, 23, 33-43.	4.0	4
2	Skin-conformable photoplethysmogram sensors for energy-efficient always-on cardiovascular monitoring systems. Nano Energy, 2022, 92, 106773.	16.0	16
3	Facile Polydimethylsiloxane Treatment of Indium Gallium Zinc Oxide Phototransistor for Visible Light-Based Multilevel Photomemory. Advanced Optical Materials, 2022, 10, .	7.3	7
4	Image quality enhancement in variable-refresh-rate AMOLED displays using a variable initial voltage compensation scheme. Scientific Reports, 2022, 12, 5977.	3.3	2
5	Performance Improvement of Self-Aligned Coplanar Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors by Boron Implantation. ACS Applied Electronic Materials, 2022, 4, 2372-2379.	4.3	7
6	Polyimide-Doped Indium-Gallium-Zinc Oxide-Based Transparent and Flexible Phototransistor for Visible Light Detection. ACS Applied Materials & Interfaces, 2022, 14, 21150-21158.	8.0	6
7	Early Career Forum in ACS Applied Electronic Materials. ACS Applied Electronic Materials, 2022, 4, 1368-1368.	4.3	0
8	In-plane optical and electrical anisotropy in low-symmetry layered GeS microribbons. NPG Asia Materials, 2022, 14, .	7.9	5
9	Realization of Enhanced Long-Term Visual Memory for Indium-Gallium-Zinc Oxide-Based Optical Synaptic Transistor. Advanced Optical Materials, 2022, 10, .	7.3	9
10	Virtual Special Issue: Halide Perovskite Materials and Applications. ACS Applied Energy Materials, 2022, 5, 7889-7890.	5.1	0
11	Mechanically Durable Organic/High-k Inorganic Hybrid Gate Dielectrics Enabled by Plasma-Polymerization of PTFE for Flexible Electronics. ACS Applied Materials & Interfaces, 2022, 14, 28085-28096.	8.0	5
12	Virtual Special Issue: Halide Perovskite Materials and Applications. ACS Applied Electronic Materials, 2022, 4, 3325-3326.	4.3	0
13	Student Paper: Widening the Wavelength Absorption Range of Indium Gallium Zinc Oxide Phototransistors through the Capping layer. Digest of Technical Papers SID International Symposium, 2022, 53, 86-89.	0.3	0
14	Student Paper: Enhanced Electrical Characteristics of Low-Temperature Processed InGaZnO Thin-Film Transistors with Oxygen Scavenging Layer. Digest of Technical Papers SID International Symposium, 2022, 53, 145-146.	0.3	0
15	Confronting Racism in Chemistry Journals. ACS ES&T Engineering, 2021, 1, 3-5.	7.6	0
16	Confronting Racism in Chemistry Journals. ACS ES&T Water, 2021, 1, 3-5.	4.6	0
17	Vertically Graded Oxygen Deficiency for Improving Electrical Characteristics and Stability of Indium Gallium Zinc Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 4110-4116.	8.0	24
18	Indium oxide nanomesh-based electrolyte-gated synaptic transistors. Journal of Information Display, 2021, 22, 179-185.	4.0	5

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19	Hydrogen Barriers Based on Chemical Trapping Using Chemically Modulated Al ₂ O ₃ Grown by Atomic Layer Deposition for InGaZnO Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 20349-20360.	8.0	15
20	Enhancement of picture quality on ultra-low brightness by optimizing the electrical potential required for OLED charging in the AMOLED displays. Journal of Information Display, 2021, 22, 275-284.	4.0	6
21	A Review of Phototransistors Using Metal Oxide Semiconductors: Research Progress and Future Directions. Advanced Materials, 2021, 33, e2006091.	21.0	67
22	Modulation of the Al/Cu ₂ O Schottky Barrier Height for p-Type Oxide TFTs Using a Polyethylenimine Interlayer. ACS Applied Materials & Interfaces, 2021, 13, 31077-31085.	8.0	12
23	Highly sensitive active pixel image sensor array driven by large-area bilayer MoS ₂ transistor circuitry. Nature Communications, 2021, 12, 3559.	12.8	94
24	Multifunctional Oxygen Scavenger Layer for High-Performance Oxide Thin-Film Transistors with Low-Temperature Processing. ACS Applied Materials & Interfaces, 2021, 13, 31816-31824.	8.0	22
25	Flexible Artificial Synapses with a Biocompatible Maltose-Ascorbic Acid Electrolyte Gate for Neuromorphic Computing. ACS Applied Materials & Interfaces, 2021, 13, 34597-34604.	8.0	19
26	Novel Method for Fabricating Visible-Light Phototransistors Based on a Homo Junction-Porous IGZO Thin Film Using Mechano-Chemical Treatment. ACS Applied Materials & Interfaces, 2021, 13, 35981-35989.	8.0	11
27	22.1: Invited Paper: Metal Oxide Semiconductor Phototransistors for Detecting Visible Light with Various Absorption Layers. Digest of Technical Papers SID International Symposium, 2021, 52, 293-293.	0.3	0
28	A Facile Method Based on Oxide Semiconductor Reduction for Controlling the Photoresponse Characteristic of Flexible and Transparent Optoelectronic Devices. Advanced Optical Materials, 2021, 9, 2100725.	7.3	12
29	Neuromorphic Active Pixel Image Sensor Array for Visual Memory. ACS Nano, 2021, 15, 15362-15370.	14.6	52
30	Biocompatible and Biodegradable Neuromorphic Device Based on Hyaluronic Acid for Implantable Bioelectronics. Advanced Functional Materials, 2021, 31, 2107074.	14.9	23
31	Photo-induced Reactive Oxygen Species Activation for Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors Using Sodium Hypochlorite. ACS Applied Materials & Interfaces, 2021, 13, 44531-44540.	8.0	8
32	Forum on Wearable and Biodegradable Sensors. ACS Applied Bio Materials, 2021, 4, 1-2.	4.6	3
33	Forum on Wearable and Biodegradable Sensors. ACS Applied Electronic Materials, 2021, 3, 1-2.	4.3	2
34	A Review of Phototransistors Using Metal Oxide Semiconductors: Research Progress and Future Directions (Adv. Mater. 47/2021). Advanced Materials, 2021, 33, 2170372.	21.0	1
35	Low-thermal-budget (300 °C) ferroelectric TiN/Hf _{0.5} Zr _{0.5} O ₂ /TiN capacitors realized using high-pressure annealing. Applied Physics Letters, 2021, 119, .	3.3	16
36	A Review of Low-Temperature Solution-Processed Metal Oxide Thin-Film Transistors for Flexible Electronics. Advanced Functional Materials, 2020, 30, 1904632.	14.9	265

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37	Flexible and Waterproof Resistive Random Access Memory Based on Nitrocellulose for Skin-Attachable Wearable Devices. <i>Advanced Functional Materials</i> , 2020, 30, 1907437.	14.9	44
38	Improving the performances of oxide phototransistors using a mechanochemically treated porous visible-light absorption layer. <i>Journal of Information Display</i> , 2020, 21, 217-222.	4.0	6
39	Multifunctional, Room-Temperature Processable, Heterogeneous Organic Passivation Layer for Oxide Semiconductor Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 2615-2624.	8.0	27
40	Fabrication of indium gallium zinc oxide phototransistors <i>via</i> oxide-mesh insertion for visible light detection. <i>Journal of Materials Chemistry C</i> , 2020, 8, 165-172.	5.5	19
41	P ₆ : Homojunction Indium-Gallium-Zinc Oxide Thin-Film Transistors by Selective Simultaneous UV and Thermal Treatment. <i>Digest of Technical Papers SID International Symposium</i> , 2020, 51, 1369-1371.	0.3	0
42	Confronting Racism in Chemistry Journals. <i>ACS Pharmacology and Translational Science</i> , 2020, 3, 559-561.	4.9	0
43	Confronting Racism in Chemistry Journals. <i>Biochemistry</i> , 2020, 59, 2313-2315.	2.5	0
44	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Biomaterials Science and Engineering</i> , 2020, 6, 2707-2708.	5.2	0
45	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Central Science</i> , 2020, 6, 589-590.	11.3	0
46	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Chemical Biology</i> , 2020, 15, 1282-1283.	3.4	0
47	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Chemical Neuroscience</i> , 2020, 11, 1196-1197.	3.5	0
48	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Earth and Space Chemistry</i> , 2020, 4, 672-673.	2.7	0
49	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Energy Letters</i> , 2020, 5, 1610-1611.	17.4	1
50	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Macro Letters</i> , 2020, 9, 666-667.	4.8	0
51	Update to Our Reader, Reviewer, and Author Communities April 2020. , 2020, 2, 563-564.		0
52	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Nano</i> , 2020, 14, 5151-5152.	14.6	2
53	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Photonics</i> , 2020, 7, 1080-1081.	6.6	0
54	Update to Our Reader, Reviewer, and Author Communities April 2020. <i>ACS Pharmacology and Translational Science</i> , 2020, 3, 455-456.	4.9	0

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55	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Sustainable Chemistry and Engineering, 2020, 8, 6574-6575.	6.7	0
56	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Analytical Chemistry, 2020, 92, 6187-6188.	6.5	0
57	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Chemistry of Materials, 2020, 32, 3678-3679.	6.7	0
58	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Environmental Science and Technology Letters, 2020, 7, 280-281.	8.7	1
59	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Journal of Chemical Education, 2020, 97, 1217-1218.	2.3	1
60	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Journal of Proteome Research, 2020, 19, 1883-1884.	3.7	0
61	Confronting Racism in Chemistry Journals. Langmuir, 2020, 36, 7155-7157.	3.5	0
62	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Applied Polymer Materials, 2020, 2, 1739-1740.	4.4	0
63	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Combinatorial Science, 2020, 22, 223-224.	3.8	0
64	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Medicinal Chemistry Letters, 2020, 11, 1060-1061.	2.8	0
65	High Photosensitive Indiumâ€”Galliumâ€”Zinc Oxide Thin-Film Phototransistor with a Selenium Capping Layer for Visible-Light Detection. ACS Applied Materials & Interfaces, 2020, 12, 10673-10680.	8.0	42
66	Pâ€—7: Improvement of Electrical Stability of Inâ€”Gaâ€”Znâ€”O Thinâ€”film Transistors by Incorporation of Polytetrafluoroethylene in the Back Channel Region. Digest of Technical Papers SID International Symposium, 2020, 51, 1334-1337.	0.3	0
67	Editorial Confronting Racism in Chemistry Journals. , 2020, 2, 829-831.		0
68	Enhancement of electrical characteristics and stability of self-patterned Inâ€”Znâ€”O thin-film transistors based on photosensitive precursors. Scientific Reports, 2020, 10, 18853.	3.3	6
69	Simultaneously Defined Semiconducting Channel Layer Using Electrohydrodynamic Jet Printing of a Passivation Layer for Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2020, 12, 39705-39712.	8.0	19
70	Gallium Doping Effects for Improving Switching Performance of p-Type Copper(I) Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2020, 12, 38350-38356.	8.0	38
71	Confronting Racism in Chemistry Journals. Journal of Physical Chemistry Letters, 2020, 11, 5279-5281.	4.6	1
72	Confronting Racism in Chemistry Journals. ACS Applied Energy Materials, 2020, 3, 6016-6018.	5.1	0

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73	Confronting Racism in Chemistry Journals. ACS Central Science, 2020, 6, 1012-1014.	11.3	1
74	Confronting Racism in Chemistry Journals. Industrial & Engineering Chemistry Research, 2020, 59, 11915-11917.	3.7	0
75	Confronting Racism in Chemistry Journals. Journal of Natural Products, 2020, 83, 2057-2059.	3.0	0
76	Confronting Racism in Chemistry Journals. ACS Medicinal Chemistry Letters, 2020, 11, 1354-1356.	2.8	0
77	Confronting Racism in Chemistry Journals. Journal of the American Society for Mass Spectrometry, 2020, 31, 1321-1323.	2.8	1
78	Confronting Racism in Chemistry Journals. Energy & Fuels, 2020, 34, 7771-7773.	5.1	0
79	Confronting Racism in Chemistry Journals. ACS Sensors, 2020, 5, 1858-1860.	7.8	0
80	Confronting Racism in Chemistry Journals. ACS Nano, 2020, 14, 7675-7677.	14.6	2
81	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. Biochemistry, 2020, 59, 1641-1642.	2.5	0
82	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. Journal of Chemical & Engineering Data, 2020, 65, 2253-2254.	1.9	0
83	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. Organic Process Research and Development, 2020, 24, 872-873.	2.7	0
84	Switching Enhancement via a Back-Channel Phase-Controlling Layer for p-Type Copper Oxide Thin-Film Transistors. ACS Applied Materials & Interfaces, 2020, 12, 24929-24939.	8.0	27
85	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. ACS Omega, 2020, 5, 9624-9625.	3.5	0
86	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. ACS Applied Electronic Materials, 2020, 2, 1184-1185.	4.3	0
87	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. ACS Applied Materials & Interfaces, 2020, 12, 20147-20148.	8.0	5
88	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. Journal of Physical Chemistry C, 2020, 124, 9629-9630.	3.1	0
89	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. Journal of Physical Chemistry Letters, 2020, 11, 3571-3572.	4.6	0
90	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. ACS Synthetic Biology, 2020, 9, 979-980.	3.8	0

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91	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Applied Energy Materials, 2020, 3, 4091-4092.	5.1	0
92	Confronting Racism in Chemistry Journals. Journal of Chemical Theory and Computation, 2020, 16, 4003-4005.	5.3	0
93	Confronting Racism in Chemistry Journals. Journal of Organic Chemistry, 2020, 85, 8297-8299.	3.2	0
94	Confronting Racism in Chemistry Journals. Analytical Chemistry, 2020, 92, 8625-8627.	6.5	0
95	Confronting Racism in Chemistry Journals. Journal of Chemical Education, 2020, 97, 1695-1697.	2.3	0
96	Confronting Racism in Chemistry Journals. Organic Process Research and Development, 2020, 24, 1215-1217.	2.7	0
97	Confronting Racism in Chemistry Journals. ACS Sustainable Chemistry and Engineering, 2020, 8, .	6.7	0
98	Confronting Racism in Chemistry Journals. Chemistry of Materials, 2020, 32, 5369-5371.	6.7	0
99	Confronting Racism in Chemistry Journals. Chemical Research in Toxicology, 2020, 33, 1511-1513.	3.3	0
100	Confronting Racism in Chemistry Journals. Inorganic Chemistry, 2020, 59, 8639-8641.	4.0	0
101	Confronting Racism in Chemistry Journals. ACS Applied Nano Materials, 2020, 3, 6131-6133.	5.0	0
102	Confronting Racism in Chemistry Journals. ACS Applied Polymer Materials, 2020, 2, 2496-2498.	4.4	0
103	Confronting Racism in Chemistry Journals. ACS Chemical Biology, 2020, 15, 1719-1721.	3.4	0
104	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Journal of Chemical Theory and Computation, 2020, 16, 2881-2882.	5.3	0
105	Confronting Racism in Chemistry Journals. Organic Letters, 2020, 22, 4919-4921.	4.6	4
106	Confronting Racism in Chemistry Journals. ACS Applied Materials & Interfaces, 2020, 12, 28925-28927.	8.0	13
107	Confronting Racism in Chemistry Journals. Crystal Growth and Design, 2020, 20, 4201-4203.	3.0	1
108	Confronting Racism in Chemistry Journals. Chemical Reviews, 2020, 120, 5795-5797.	47.7	2

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109	Confronting Racism in Chemistry Journals. ACS Catalysis, 2020, 10, 7307-7309.	11.2	1
110	Confronting Racism in Chemistry Journals. Biomacromolecules, 2020, 21, 2543-2545.	5.4	0
111	Confronting Racism in Chemistry Journals. Journal of Medicinal Chemistry, 2020, 63, 6575-6577.	6.4	0
112	Confronting Racism in Chemistry Journals. Macromolecules, 2020, 53, 5015-5017.	4.8	0
113	Confronting Racism in Chemistry Journals. Nano Letters, 2020, 20, 4715-4717.	9.1	5
114	Confronting Racism in Chemistry Journals. Organometallics, 2020, 39, 2331-2333.	2.3	0
115	Confronting Racism in Chemistry Journals. Journal of the American Chemical Society, 2020, 142, 11319-11321.	13.7	1
116	Mechanochemical and Thermal Treatment for Surface Functionalization to Reduce the Activation Temperature of In-Ga-Zn-O Thin-film Transistors. ACS Applied Materials & Interfaces, 2020, 12, 19123-19129.	8.0	18
117	Confronting Racism in Chemistry Journals. Accounts of Chemical Research, 2020, 53, 1257-1259.	15.6	0
118	Confronting Racism in Chemistry Journals. Journal of Physical Chemistry A, 2020, 124, 5271-5273.	2.5	0
119	Confronting Racism in Chemistry Journals. ACS Energy Letters, 2020, 5, 2291-2293.	17.4	0
120	Confronting Racism in Chemistry Journals. Journal of Chemical Information and Modeling, 2020, 60, 3325-3327.	5.4	0
121	Confronting Racism in Chemistry Journals. Journal of Proteome Research, 2020, 19, 2911-2913.	3.7	0
122	Confronting Racism in Chemistry Journals. Journal of Physical Chemistry B, 2020, 124, 5335-5337.	2.6	1
123	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Journal of Agricultural and Food Chemistry, 2020, 68, 5019-5020.	5.2	0
124	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. Journal of Physical Chemistry B, 2020, 124, 3603-3604.	2.6	0
125	Confronting Racism in Chemistry Journals. Bioconjugate Chemistry, 2020, 31, 1693-1695.	3.6	0
126	Update to Our Reader, Reviewer, and Author Communitiesâ€”April 2020. ACS Applied Nano Materials, 2020, 3, 3960-3961.	5.0	0

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127	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Journal of Natural Products, 2020, 83, 1357-1358.	3.0	0
128	Confronting Racism in Chemistry Journals. ACS Synthetic Biology, 2020, 9, 1487-1489.	3.8	0
129	Confronting Racism in Chemistry Journals. Journal of Chemical & Engineering Data, 2020, 65, 3403-3405.	1.9	0
130	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Bioconjugate Chemistry, 2020, 31, 1211-1212.	3.6	0
131	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Journal of Chemical Health and Safety, 2020, 27, 133-134.	2.1	0
132	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Chemical Research in Toxicology, 2020, 33, 1509-1510.	3.3	0
133	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Energy & Fuels, 2020, 34, 5107-5108.	5.1	0
134	Improvement of the stability and optoelectronic characteristics of molybdenum disulfide thin-film transistors by applying a nitrocellulose passivation layer. Journal of Information Display, 2020, 21, 123-130.	4.0	9
135	Young Investigator Forum in ACS Applied Electronic Materials. ACS Applied Electronic Materials, 2020, 2, 1-1.	4.3	0
136	Near-field sub-diffraction photolithography with an elastomeric photomask. Nature Communications, 2020, 11, 805.	12.8	36
137	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. ACS Applied Bio Materials, 2020, 3, 2873-2874.	4.6	0
138	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Journal of Organic Chemistry, 2020, 85, 5751-5752.	3.2	0
139	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Journal of the American Society for Mass Spectrometry, 2020, 31, 1006-1007.	2.8	0
140	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Accounts of Chemical Research, 2020, 53, 1001-1002.	15.6	0
141	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Biomacromolecules, 2020, 21, 1966-1967.	5.4	0
142	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Chemical Reviews, 2020, 120, 3939-3940.	47.7	0
143	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Environmental Science & Technology, 2020, 54, 5307-5308.	10.0	0
144	Update to Our Reader, Reviewer, and Author Communitiesâ€™April 2020. Langmuir, 2020, 36, 4565-4566.	3.5	0

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145	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Molecular Pharmaceutics</i> , 2020, 17, 1445-1446.	4.6	0
146	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>ACS Infectious Diseases</i> , 2020, 6, 891-892.	3.8	0
147	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Crystal Growth and Design</i> , 2020, 20, 2817-2818.	3.0	1
148	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Journal of Medicinal Chemistry</i> , 2020, 63, 4409-4410.	6.4	0
149	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Journal of Physical Chemistry A</i> , 2020, 124, 3501-3502.	2.5	0
150	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Nano Letters</i> , 2020, 20, 2935-2936.	9.1	0
151	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>ACS Sensors</i> , 2020, 5, 1251-1252.	7.8	0
152	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Journal of Chemical Information and Modeling</i> , 2020, 60, 2651-2652.	5.4	0
153	Highâ€performance vacuumâ€processed metal oxide thinâ€film transistors: A review of recent developments. <i>Journal of the Society for Information Display</i> , 2020, 28, 591-622.	2.1	28
154	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Industrial & Engineering Chemistry Research</i> , 2020, 59, 8509-8510.	3.7	0
155	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Journal of the American Chemical Society</i> , 2020, 142, 8059-8060.	13.7	3
156	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Inorganic Chemistry</i> , 2020, 59, 5796-5797.	4.0	0
157	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Organometallics</i> , 2020, 39, 1665-1666.	2.3	0
158	Update to Our Reader, Reviewer, and Author Communitiesâ€™ April 2020. <i>Organic Letters</i> , 2020, 22, 3307-3308.	4.6	0
159	Confronting Racism in Chemistry Journals. <i>ACS Biomaterials Science and Engineering</i> , 2020, 6, 3690-3692.	5.2	1
160	Confronting Racism in Chemistry Journals. <i>ACS Omega</i> , 2020, 5, 14857-14859.	3.5	1
161	Confronting Racism in Chemistry Journals. <i>ACS Applied Electronic Materials</i> , 2020, 2, 1774-1776.	4.3	0
162	Confronting Racism in Chemistry Journals. <i>Journal of Agricultural and Food Chemistry</i> , 2020, 68, 6941-6943.	5.2	0

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163	Confronting Racism in Chemistry Journals. ACS Earth and Space Chemistry, 2020, 4, 961-963.	2.7	0
164	Confronting Racism in Chemistry Journals. Environmental Science and Technology Letters, 2020, 7, 447-449.	8.7	0
165	Confronting Racism in Chemistry Journals. ACS Combinatorial Science, 2020, 22, 327-329.	3.8	0
166	Confronting Racism in Chemistry Journals. ACS Infectious Diseases, 2020, 6, 1529-1531.	3.8	0
167	Confronting Racism in Chemistry Journals. ACS Applied Bio Materials, 2020, 3, 3925-3927.	4.6	0
168	Confronting Racism in Chemistry Journals. Journal of Physical Chemistry C, 2020, 124, 14069-14071.	3.1	0
169	Confronting Racism in Chemistry Journals. ACS Macro Letters, 2020, 9, 1004-1006.	4.8	0
170	Confronting Racism in Chemistry Journals. Molecular Pharmaceutics, 2020, 17, 2229-2231.	4.6	1
171	Confronting Racism in Chemistry Journals. ACS Chemical Neuroscience, 2020, 11, 1852-1854.	3.5	1
172	Confronting Racism in Chemistry Journals. ACS Photonics, 2020, 7, 1586-1588.	6.6	0
173	Confronting Racism in Chemistry Journals. Environmental Science & Technology, 2020, 54, 7735-7737.	10.0	0
174	Confronting Racism in Chemistry Journals. Journal of Chemical Health and Safety, 2020, 27, 198-200.	2.1	0
175	Balanced Performance Enhancements of InGaZnO Thin Film Transistors by Using All-Amorphous Dielectric Multilayers Sandwiching High- κ $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$. Advanced Electronic Materials, 2019, 5, 1900322.	5.1	5
176	Artificially Fabricated Subgap States for Visible-Light Absorption in Indium-Gallium-Zinc Oxide Phototransistor with Solution-Processed Oxide Absorption Layer. ACS Applied Materials & Interfaces, 2019, 11, 38964-38972.	8.0	32
177	Glucose-based resistive random access memory for transient electronics. Journal of Information Display, 2019, 20, 231-237.	4.0	12
178	Introducing ACS Applied Electronic Materials. ACS Applied Electronic Materials, 2019, 1, 1-1.	4.3	2
179	News Paper: Alleviation of Recoverable Residual Image Phenomenon of Flexible Organic Light-Emitting Diode Display. Digest of Technical Papers SID International Symposium, 2019, 50, 105-108.	0.3	5
180	Improving Switching Characteristics of p-type Copper Oxide Thin-film Transistors by Germanium Oxide Passivation through Reactive Sputtering. Digest of Technical Papers SID International Symposium, 2019, 50, 1279-1282.	0.3	1

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